Small-Signal Admittance (Mathematical Analysis)

 $V_a = V_0 + v_1(t)(V_0)$ is the dc quiescent bias voltage) we can assume steady state solution for δp_n to be of the form:

$$p_{n}(0,t) = p_{n0} \exp \left\{ \frac{e \left[V_{0} + v_{1}(t)\right]}{kT} \right\} = p_{dc} \exp \frac{ev_{1}(t)}{kT} \frac{\delta p_{n}(x,t) = \delta p_{0}(x) + p_{1}(x)e^{j\omega t}}{kT};$$

$$\delta p_{0} \text{ is the dc excess carrier concentration same as previous;}$$

assume $|v_1(t)| \ll (kT/e) = V_t$

then using taylor's expansion

$$p_{n}(0,t) \approx p_{dc} \left[1 + \frac{v_{1}(t)}{V_{t}} \right] = p_{dc} \left[1 + \frac{\hat{V}_{1}}{V_{t}} e^{j\omega t} \right]$$

In neutral n region (x>0), E=0

$$D_{p} \frac{\partial^{2} (\delta p_{n})}{\partial x^{2}} - \frac{\delta p_{n}}{\tau_{p0}} = \frac{\partial (\delta p_{n})}{\partial t}$$

$$\delta p_n(x,t) = \delta p_0(x) + p_1(x)e^{j\omega t};$$

p₁ is magnitude of ac component of excess carrier

$$D_{p} \left\{ \frac{\partial^{2} \left[\delta p_{0}(x) \right]}{\partial x^{2}} + \frac{\partial^{2} p_{1}(x)}{\partial x^{2}} e^{j\omega t} \right\} - \frac{\delta p_{0}(x) + p_{1}(x) e^{j\omega t}}{\tau_{p0}}$$

 $= j\omega p_1(x)e^{j\omega t}$

Re write

$$\left\{\frac{D_{p}\partial^{2}\left[\delta p_{0}(x)\right]}{\partial x^{2}} - \frac{\delta p_{0}(x)}{\tau_{p0}}\right\} + \left[D_{p}\frac{\partial^{2} p_{1}(x)}{\partial^{2} x^{2}} - \frac{p_{1}(x)}{\tau_{p0}} - j\omega p_{1}(x)\right]e^{j\omega t}$$

Same as DC

Small-Signal Admittance(Mathematical Analysis)

$$\begin{split} &\left\{\frac{D_{p}\hat{\sigma}^{2}\left[\delta p_{0}\left(x\right)\right]}{\partial x^{2}}-\frac{\delta p_{0}\left(x\right)}{\tau_{p0}}\right\}+\left[D_{p}\frac{\partial^{2} p_{1}\left(x\right)}{\partial^{2} x^{2}}-\frac{p_{1}\left(x\right)}{\tau_{p0}}-j\omega p_{1}\left(x\right)\right]e^{j\omega t}\\ &=0 & J_{p}=-eD_{p}\frac{\partial p_{n}}{\partial x}\big|_{x=0}=-eD_{p}\frac{\partial \delta p_{n}}{\partial x}\big|_{x=0}\\ &D_{p}\frac{\partial^{2} p_{1}\left(x\right)}{\partial^{2} x^{2}}-\frac{p_{1}\left(x\right)}{\tau_{p0}}-j\omega p_{1}\left(x\right)=0 & =-eD_{p}\frac{\partial \delta p_{0}\left(x\right)}{\partial x}\big|_{x=0}-eD_{p}\frac{\partial p_{1}\left(x\right)}{\partial x}\big|_{x=0}e^{j\omega t}\\ &\frac{d^{2} p_{1}\left(x\right)}{d^{2} x^{2}}-\frac{\left(1+j\omega \tau_{p0}\right)}{L_{p}^{2}}p_{1}\left(x\right)=\frac{d^{2} p_{1}\left(x\right)}{d^{2} x^{2}}-C_{p}^{2} p_{1}\left(x\right)=0 & J_{p}=J_{p0}+j_{p}\left(t\right)\\ p_{1}\left(x\right)=K_{1}e^{-C_{p}x}+K_{2}e^{C_{p}x} & \text{where } J_{p0}=-eD_{p}\frac{\partial \delta p_{0}\left(x\right)}{\partial x}\big|_{x=0}=\frac{eD_{p}p_{n0}}{L_{p}}\left[\exp\left(\frac{eV_{a}}{kT}\right)-1\right]\\ B.C. \begin{cases} p_{1}\left(x\right)=K_{1}e^{-C_{p}x}\left(p_{1}\left(x\rightarrow+\infty\right)=0\right)\\ p_{1}\left(0\right)=K_{1}=p_{dc}\left(\frac{\hat{V_{1}}}{V_{t}}\right) & j_{p}\left(t\right)=\hat{J}_{p}e^{j\omega t}=-eD_{p}\left(\frac{\hat{V_{1}}}{V_{t}}\right)\Big|_{x=0}e^{j\omega t}\\ \hat{J}_{p}=-eD_{p}\left(-C_{p}\right)\left[p_{dc}\left(\frac{\hat{V_{1}}}{V_{t}}\right)\right]e^{-C_{p}x}\big|_{x=0} \end{split}$$

Small-Signal Admittance(Mathematical Analysis)

$$\hat{J}_{p} = -eD_{p}\left(-C_{p}\right)\left[p_{dc}\left(\frac{\hat{V}_{1}}{V_{t}}\right)\right]e^{-C_{p}x}\big|_{x=0}$$

$$\hat{I}_{p} = A\hat{J}_{p} = eAD_{p}C_{p}p_{dc}\left(\frac{\hat{V}_{1}}{V_{t}}\right) = \frac{eAD_{p}p_{dc}}{L_{p}}\sqrt{1 + j\omega\tau_{p0}}\left(\frac{\hat{V}_{1}}{V_{t}}\right) = \left(\frac{1}{V_{t}}\right)\left[I_{p0}\sqrt{1 + j\omega\tau_{p0}} + I_{n0}\sqrt{1 + j\omega\tau_{n0}}\right]$$

$$=I_{p0}\sqrt{1+j\omega\tau_{p0}}\left(\frac{\hat{V_1}}{V_t}\right)$$

Going through the same type of analysis for the minority carrier electrons in the p region

$$\hat{I}_{n} = I_{n0}\sqrt{1 + j\omega\tau_{n0}} \left(\frac{\hat{V}_{1}}{V_{t}}\right) \text{ where } I_{n0} = \frac{eAD_{n}n_{p0}}{L_{n}} \exp\left(\frac{eV_{0}}{kT}\right) Y = \left(\frac{1}{V_{t}}\right) \left[I_{p0}\left(1 + \frac{j\omega\tau_{p0}}{2}\right) + I_{n0}\left(1 + \frac{j\omega\tau_{n0}}{2}\right)\right]$$

$$Y = \frac{\hat{I}}{\hat{V_1}} = \frac{I_p + I_n}{\hat{V_1}}$$

$$\frac{1}{1 + i\omega \tau_{n0}} \left(\frac{\hat{V_1}}{\hat{V_1}}\right) = \frac{1}{1 + i\omega \tau_{n0}} \left(\frac{1}{1 + i\omega \tau_{n0}}\right)$$

Frequency of the ac signal is not too large:

$$\omega \tau_{p0} \ll 1; \omega \tau_{n0} \ll 1$$

$$\sqrt{1+j\omega\tau_{p0}} \approx 1+\frac{j\omega\tau_{p0}}{2}; \sqrt{1+j\omega\tau_{n0}} \approx 1+\frac{j\omega\tau_{n0}}{2}$$

$$Y = \left(\frac{1}{V_t}\right) \left[I_{p0}\left(1 + \frac{j\omega\tau_{p0}}{2}\right) + I_{n0}\left(1 + \frac{j\omega\tau_{n0}}{2}\right)\right]$$

$$= \left(\frac{1}{V_t}\right) \left(I_{p0} + I_{n0}\right) + j\omega \left[\left(\frac{1}{2V_t}\right) \left(I_{p0}\tau_{p0} + I_{n0}\tau_{n0}\right)\right]$$

Small-Signal Admittance(Mathematical Analysis)

$$Y = \left(\frac{1}{V_t}\right) \left(I_{p0} + I_{n0}\right) + j\omega \left[\left(\frac{1}{2V_t}\right) \left(I_{p0}\tau_{p0} + I_{n0}\tau_{n0}\right)\right]$$

$$= g_d + j\omega C_d$$

$$g_d \text{ is called the diffusion conductance and given by}$$

$$g_d = \left(\frac{1}{V_t}\right) \left(I_{p0} + I_{n0}\right) = \frac{I_{DQ}}{V_t}$$

$$C_d = \left(\frac{1}{2V_t}\right) \left(I_{p0}\tau_{p0} + I_{n0}\tau_{n0}\right)$$

Figure 8.21 | Minority carrier concentration changes with changing forward-bias voltage.

x = 0

EXAMPLE 8.7

Objective: Calculate the small-signal admittance parameters of a pn junction diode.

This example is intended to give an indication of the magnitude of the diffusion capacitance as compared with the junction capacitance considered in the last chapter. The diffusion resistance will also be calculated. Assume that $N_a \gg N_d$ so that $p_{n0} \gg n_{p0}$. This assumption implies that $I_{p0} \gg I_{n0}$. Let T = 300 K, $\tau_{p0} = 10^{-7}$ s, and $I_{p0} = I_{DQ} = 1$ mA.

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The diffusion capacitance, with these assumptions, is given by

$$C_d \approx \left(\frac{1}{2V_t}\right) (I_{p0}\tau_{p0}) = \frac{1}{(2)(0.0259)} (10^{-3})(10^{-7}) = 1.93 \times 10^{-9} \,\mathrm{F}$$

The diffusion resistance is

$$r_d = \frac{V_t}{I_{DO}} = \frac{0.0259 \text{ V}}{1 \text{ mA}} = 25.9 \Omega$$